8. (amended) A method as claimed in claim 1, wherein the semiconductor devices are separated by means of an etching treatment in a surface region of the semiconductor substrate.

9. (amended) A method as claimed in claim 1, wherein the semiconductor devices are provided in a semiconductor layer on an insulating layer (19) and are separated by means of an etching treatment.

10. (amended) A method as claimed in claim 1, wherein the substrate is flexible.

15. (amended) A method as claimed in claim 11, wherein the semiconductor devices have the same pitch as the functional groups in at least one dimension.

REMARKS

The foregoing amendments to the claims were made solely to avoid filing the claims in the multiple dependent form so as to avoid the additional filing fee.

The claims were not amended in order to address issues of patentability and Applicants respectfully reserve all rights they may have under the Doctrine of Equivalents. Applicants furthermore

reserve their right to reintroduce subject matter deleted herein at a later time during the prosecution of this application or continuing applications.

Respectfully submitted,

By

Michael E. Marion, Reg. 32,266
Attorney
(914) 333-9641

APPENDIX

5. (amended) A method as claimed in claim 1~~ or 3~~, wherein the semiconductor devices have the same pitch as the groups of pixels in at least one dimension.

6. (amended) A method as claimed in claim 1~~ or 3~~, wherein a semiconductor device is associated with a plurality of pixels.

8. (amended) A method as claimed in claim 1~~ or 3~~, wherein the semiconductor devices are separated by means of an etching treatment in a surface region of the semiconductor substrate.

9. (amended) A method as claimed in claim 1~~ or 3~~, wherein the semiconductor devices are provided in a semiconductor layer on an insulating layer (19) and are separated by means of an etching treatment.

10. (amended) A method as claimed in claim 1~~ or 3~~, wherein the substrate is flexible.

15. (amended) A method as claimed in claim 11~~ or 13~~, wherein the semiconductor devices have the same pitch as the functional groups in at least one dimension.